

S/N 09/135,413

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: Viet Q. Nguyen

Serial No.: 09/135,413

Group Art Unit: 2818

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Title: METHOD FOR OPERATING A TRANSISTOR FROM HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR



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3-23-00

L. Spruell

AMENDMENT AND RESPONSE

Assistant Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on December 13, 1999. Please amend the above-identified patent application as follows.

IN THE CLAIMS

Please amend the following claim:

29. (Twice Amended) The method of claim 28 wherein programming [the] a floating gate [transistor] electrode further comprises causing hot electron injection from the channel through an amorphous silicon carbide (a-SiC) gate insulator to the floating gate electrode.

Please add the following new claims:

64. (New) A method of using a floating gate transistor, comprising:

programming a floating gate electrode of the floating gate transistor by placing a charge on the floating gate electrode, wherein the floating gate transistor has a barrier energy between the floating gate electrode and a silicon carbide (SiC) gate insulator separating the floating gate electrode from a substrate, the barrier energy being less than approximately 3.3 eV;

reading the floating gate transistor by placing a read voltage on a control gate and detecting current in a channel between a source region and a drain region in the substrate; and erasing the floating gate transistor.